

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







Plastic Infrared Emitting Diode

OP265FAA Series



Features:

- T-1 (3 mm) package style
- Narrow irradiance pattern
- Dome lens
- Higher power output than GaAs at equivalent drive currents
- 850 nm diode



Description:

Each device in the **OP265FAA** series is a high intensity gallium arsenide infrared emitting diode (GaAlAs) that is molded in an IR transmissive clear epoxy package with a dome lens. Devices feature a narrow source irradiance pattern and a variety of electrical characteristics. The small T-1 package style makes these devices ideal for space-limited applications.

These devices are mechanically and spectrally matched to other OPTEK products as follows:

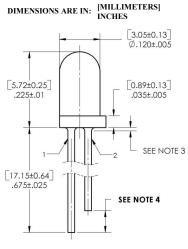
OP265 devices conform to the OP505 and OP535 series devices.

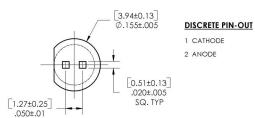
Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

- Space-limited applications
- · Applications requiring coupling efficiency
- Battery-operated or voltage-limited applications

Ordering Information									
Part LED Peak Output Power (mW Number Wavelength Min / Max		Output Power (mW/cm²) Min / Max	I _F (mA) Typ / Max	Total Beam Angle	Lead Length				
OP265FAA		5.5 / NA		18°	0.50"				
OP265FAB	850 nm	7.5 / 12.5	20 / 50						
OP265FAC		11.5 / 16.5							







IMPORTANT: For identification purposes, ANODE lead is shorter that the CATHODE lead in order to differentiate this product from regular OP265 and/or OP313.

Pin #	LED		
1	Cathode		
2	Anode		

NOTES:

- OUTSIDE DISCRETE SHELL IS POLYSULFONE P1700 CLEAR.
- 2. THIS LED IS BUILT WITH A 850nm CHIP.
- MAX ALLOWABLE EPOXY MINISCUS IS 0.030.
- 4. FOR IDENTIFICATION PURPOSES, ANODE LEAD IS .065 \pm .035 **SHORTER** THAN THE CATHODE LEAD.

CONTAINS POLYSULFONE

To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK'S molded plastics.

General Note

Plastic Infrared Emitting Diode

OP265FAA Series



Electrical Specifications

bsolute Maximum Ratings (T _A = 25° C unless otherwise noted)				
Storage and Operating Temperature Range	-40° C to +100° C			
Reverse Voltage	2.0 V			
Continuous Forward Current	50 mA			
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A			
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾			
Power Dissipation	100 mW ⁽²⁾			

Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 second maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.
- 2. Derate linearly at 1.33 mW/° C above 25° C.
- 3. E_{E(APT)} is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens and 0.590" (14.99 mm) from the measurement surface. E_{E(APT)} is not necessarily uniform within the measured area.

Electrical Characteristics (T _A = 25° C unless otherwise noted)								
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
Input Diode								
E _{E (APT)}	Apertured Radiant Incidence OP265FAA OP265FAB OP265FAC	5.50 7.50 11.50	- - -	- 12.5 16.5	mW/cm²	I_{F} = 20 mA Aperture = 0.081" diameter Distance = 0.590" from seating surface to aperture surface		
V_{F}	Forward Voltage	-	-	1.80	V	I _F = 20 mA		
I _R	Reverse Current	-	10	-	μΑ	V _R = 10 V		
λ_{P}	Wavelength at Peak Emission	-	850	-	nm	I _F = 10 mA		
$\Delta\lambda_P/\Delta T$	Spectral Shift with Temperature	-	±0.18	-	nm/°C	I _F = Constant		
θ_{HP}	Emission Angle at Half Power Points	-	18	-	Degree	I _F = 20 mA		
t _r	Output Rise Time	-	10	-	ns	I _{F(PK)} =100 mA, PW=10 μs, D.C.=10.0%		
t _f	Output Fall Time	-	10	-	ns			

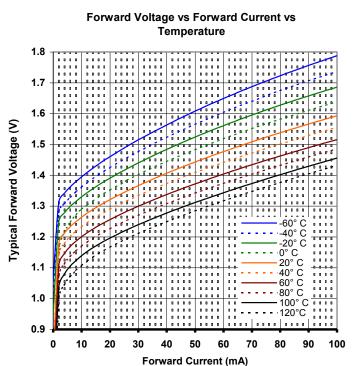
Issue F 07/2016 Page 2

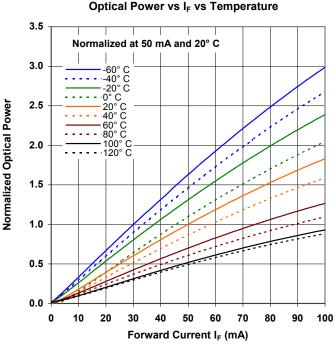
Plastic Infrared Emitting Diode

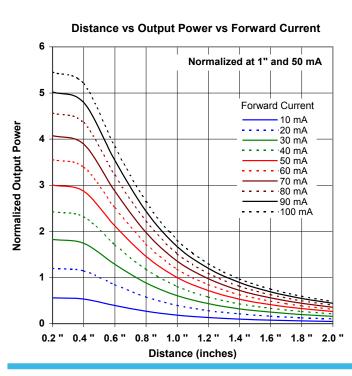
OP265FAA Series

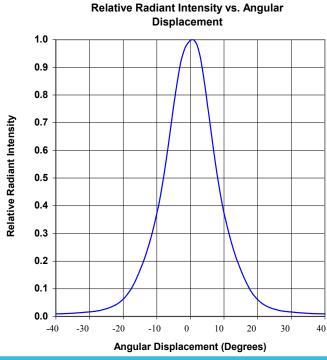


Performance OP265F (AA, AB, AC)









General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.